



PRODUCT NAME : 2N6342 8A 200V TRIAC

PRICE : Rs 35.00

SKU : RM1982



DESCRIPTION

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Features

- Gate Turn-On Voltage (Vgt): 1.1V
- Peak Off-State Voltage(Vdrm): 200V
- On-State Current (It): 8.0A
- Gate Current (Igt): 35mA

MOTOROLA
SEMICONDUCTOR TECHNICAL DATA

Order this document
 by 2N6342/D

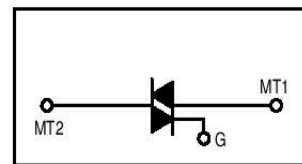
Triacs
Silicon Bidirectional Triode Thyristors

... designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Two Modes (2N6342, 2N6343, 2N6344, 2N6345) or Four Modes (2N6346, 2N6347, 2N6348, 2N6349)
- For 400 Hz Operation, Consult Factory
- 12 Ampere Devices Available as 2N6342A thru 2N6349A

**2N6342
 thru
 2N6349**

**TRIACS
 8 AMPERES RMS
 200 thru 800 VOLTS**



MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Rating	Symbol	Value	Unit
*Peak Repetitive Off-State Voltage ⁽¹⁾ (Gate Open, $T_J = -40$ to $+110^\circ\text{C}$) 1/2 Sine Wave 50 to 60 Hz, Gate Open	V_{DRM}	200 400 600 800	Volts
*RMS On-State Current Full Cycle Sine Wave 50 to 60 Hz	$I_T(\text{RMS})$	8 4	Amps
*Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, $T_C = +80^\circ\text{C}$) Preceded and followed by Rated Current	I_{TSM}	100	Amps
Circuit Fusing ($t = 8.3$ ms)	I^2t	40	A^2s
*Peak Gate Power ($T_C = +80^\circ\text{C}$, Pulse Width = $2 \mu\text{s}$)	P_{GM}	20	Watts
*Average Gate Power ($T_C = +80^\circ\text{C}$, $t = 8.3$ ms)	$P_{G(AV)}$	0.5	Watt
*Peak Gate Current	I_{GM}	2	Amps
*Peak Gate Voltage	V_{GM}	10	Volts
*Operating Junction Temperature Range	T_J	-40 to +125	$^\circ\text{C}$
*Storage Temperature Range	T_{stg}	-40 to +150	$^\circ\text{C}$

1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

REV 1



2N6342 thru 2N6349

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, and Either Polarity of MT2 to MT1 Voltage, unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
*Peak Blocking Current ($V_D = \text{Rated } V_{DRM}$, gate open) $T_J = 25^\circ\text{C}$ $T_J = 100^\circ\text{C}$	I_{DRM}	—	—	10 2	μA mA
*Peak On-State Voltage ($I_{TM} = 11 \text{ A Peak}$; Pulse Width = 1 to 2 ms, Duty Cycle $\leq 2\%$)	V_{TM}	—	1.3	1.55	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ Vdc}$, $R_L = 100 \text{ Ohms}$) (Minimum Gate Pulse Width = 2 μs) MT2(+), G(+) All Types MT2(+), G(-) 2N6346 thru 49 MT2(-), G(-) All Types MT2(-), G(+) 2N6346 thru 49 *MT2(+), G(+); MT2(-), G(-) $T_C = -40^\circ\text{C}$ All Types *MT2(+), G(-); MT2(-), G(+) $T_C = -40^\circ\text{C}$ 2N6346 thru 49	I_{GT}	—	12 12 20 35 — —	50 75 50 75 100 125	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}$, $R_L = 100 \text{ Ohms}$) (Minimum Gate Pulse Width = 2 μs) MT2(+), G(+) All Types MT2(+), G(-) 2N6346 thru 49 MT2(-), G(-) All Types MT2(-), G(+) 2N6346 thru 49 *MT2(+), G(+); MT2(-), G(-) $T_C = -40^\circ\text{C}$ All Types *MT2(+), G(-); MT2(-), G(+) $T_C = -40^\circ\text{C}$ 2N6346 thru 49 ($V_D = \text{Rated } V_{DRM}$, $R_L = 10 \text{ k Ohms}$, $T_J = 100^\circ\text{C}$) *MT2(+), G(+); MT2(-), G(-) All Types *MT2(+), G(-); MT2(-), G(-) 2N6346 thru 49	V_{GT}	—	0.9 0.9 1.1 1.4 — —	2 2.5 2 2.5 2.5 3	Volts
*Holding Current ($V_D = 12 \text{ Vdc}$, Gate Open) $T_C = 25^\circ\text{C}$ ($I_T = 200 \text{ mA}$) $*T_C = -40^\circ\text{C}$	I_H	—	6 —	40 75	mA
*Turn-On Time ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 11 \text{ A}$, $I_{GT} = 120 \text{ mA}$, Rise Time = 0.1 μs , Pulse Width = 2 μs)	t_{gt}	—	1.5	2	μs
Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}$, $I_{TM} = 11 \text{ A}$, Commutating $di/dt = 4.0 \text{ A/ms}$, Gate Unenergized, $T_C = 80^\circ\text{C}$)	$dv/dt(c)$	—	5	—	V/ μs

*Indicates JEDEC Registered Data.

FIGURE 1 – RMS CURRENT DERATING

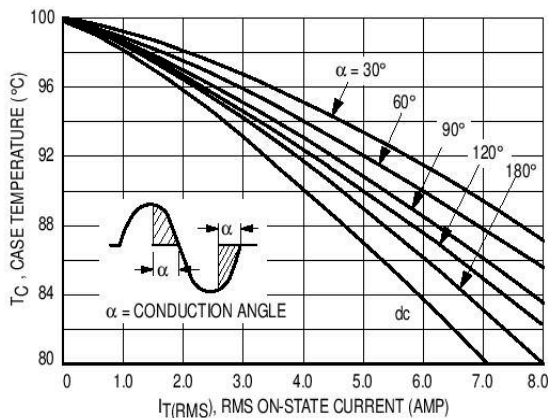


FIGURE 2 – ON-STATE POWER DISSIPATION

